Elektronische Bauelemente

SST2605

-4.0A, -30V,$R_{DS(ON)}$ 80mΩ

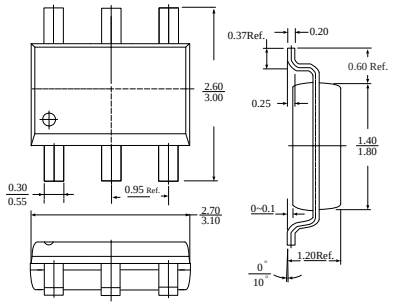
P-Channel Enhancement Mode Power Mos.FET

RoHS Compliant Product

SOT-26

Description

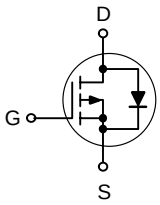
The SST2605 utiltzed advance processing techniques to achieve the lowest possible on-resistance, extermely efficient and cost-effectiveness device.
The SST2605 is universally used for all commercial-industrial applications.

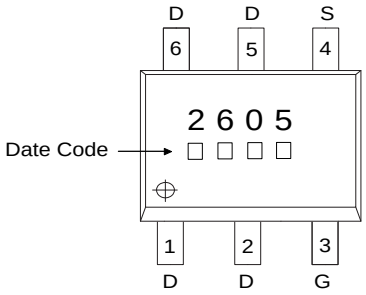


Dimensions in millimeters

Features

* Fast Switching Characteristic
* Lower Gate Charge
* Small Footprint & Low Profile Package





Absolute Maximum Ratings

Parameter	Symbol	Ratings	Unit
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	±20	V
Continuous Drain Current [3]	I_D@T_A=25 °C	-4.0	A
Continuous Drain Current [3]	I_D@T_A=70 °C	-3.3	A
Pulsed Drain Current [1]	I_{DM}	-20	A
Total Power Dissipation	P_D@T_A=25 °C	2.0	W
Linear Derating Factor		0.016	W/°C
Operating Junction and Storage Temperature Range	Tj, Tstg	-55~+150	°C

Thermal Data

Parameter	Symbol	Ratings	Unit
Thermal Resistance Junction-ambient [3]	Rthj-a	62.5	°C/W

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Electrical Characteristics(Tj=25°C Unless otherwise specified)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Condition
Drain-Source Breakdown Voltage	BV_{DSS}	-30	–	–	V	V_{GS}=0V, I_D=-250uA
Breakdown Voltage Temp. Coefficient	$\triangle BV_{DS}/\triangle Tj$	–	-0.02	–	V/℃	Reference to 25℃,I_D=-1mA
Gate Threshold Voltage	$V_{GS(th)}$	-1.0	–	-3.0	V	V_{DS}=V_{GS}, I_D=-250uA
Gate-Source Leakage Current	I_{GSS}	–	–	±100	nA	V_{GS}=±20V
Drain-Source Leakage Current (Tj=25℃)	I_{DSS}	–	–	-1	uA	V_{DS}=-30V,V_{GS}=0
Drain-Source Leakage Current (Tj=55℃)		–	–	-25	uA	V_{DS}=-24V,V_{GS}=0
Static Drain-Source On-Resistance [2]	$R_{DS(ON)}$	–	–	80	mΩ	V_{GS}=-10V, I_D=-4.0A
		–	–	120		V_{GS}=-4.5V, I_D=-3.0A
Total Gate Charge [2]	Qg	–	5.5	8.8	nC	I_D=-4.0A V_{DS}=-24V V_{GS}=-4.5V
Gate-Source Charge	Qgs	–	1	–		
Gate-Drain ("Miller") Charge	Qgd	–	2.6	–		
Turn-on Delay Time [2]	$Td_{(ON)}$	–	7	–	nS	V_{DD}=-15V I_D=-1A V_{GS}=-10V R_G=3.3Ω R_D=15 Ω
Rise Time	Tr	–	6	–		
Turn-off Delay Time	$Td_{(Off)}$	–	18	–		
Fall Time	T_f	–	4	–		
Input Capacitance	Ciss	–	400	640	pF	V_{GS}=0V V_{DS}=-25V f=1.0MHz
Output Capacitance	Coss	–	90	–		
Reverse Transfer Capacitance	Crss	–	30	–		
Forward Transconductance	Gfs	–	6	–	S	V_{DS}=-5V, I_D=-4.0A

Source-Drain Diode

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Condition
Forward On Voltage [2]	V_{DS}	–	–	-1.2	V	I_S=-1.6A, V_{GS}=0V.
Reverse Recovery Time [2]	Trr	–	21	–	nS	I_S=-4.0A, V_{GS}=0V dI/dt=100A/us
Reverse Recovery Charge	Qrr	–	14	–	nC	

Notes: 1.Pulse width limited by safe operating area.

2.Pulse width≦300us, dutycycle≦2%.

3.Surface mounted on 1 in² copper pad of FR4 board; 156°C/W when mounted on Min. copper pad.

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Characteristics Curve

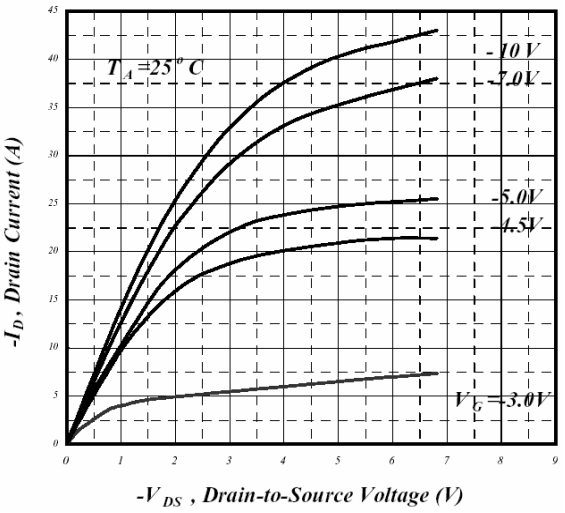

Fig 1. Typical Output Characteristics

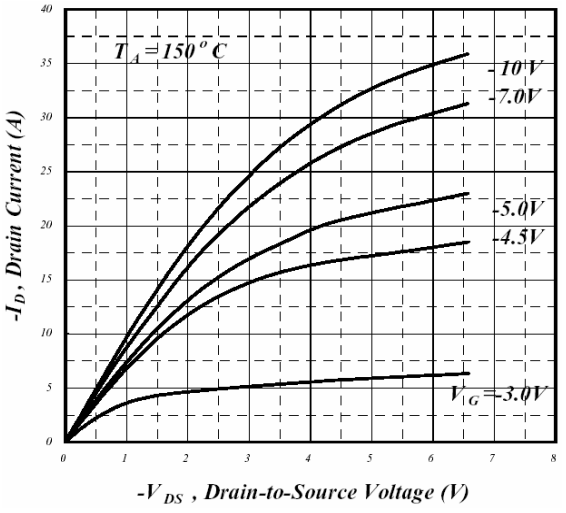

Fig 2. Typical Output Characteristics

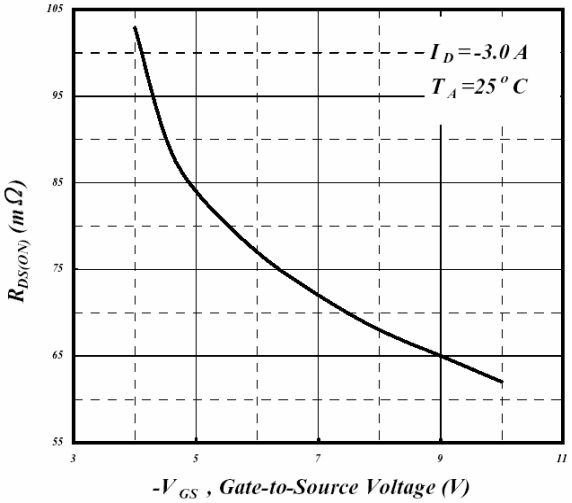

Fig 3. On-Resistance v.s. Gate Voltage

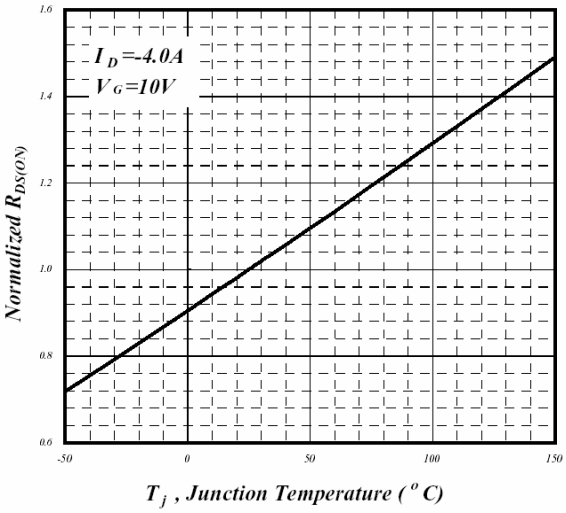

Fig 4. Normalized On-Resistance v.s. Junction Temperature

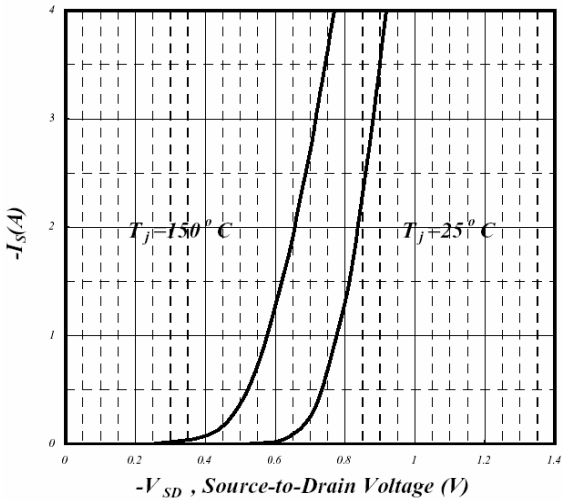

Fig 5. Forward Characteristics of Reverse Diode

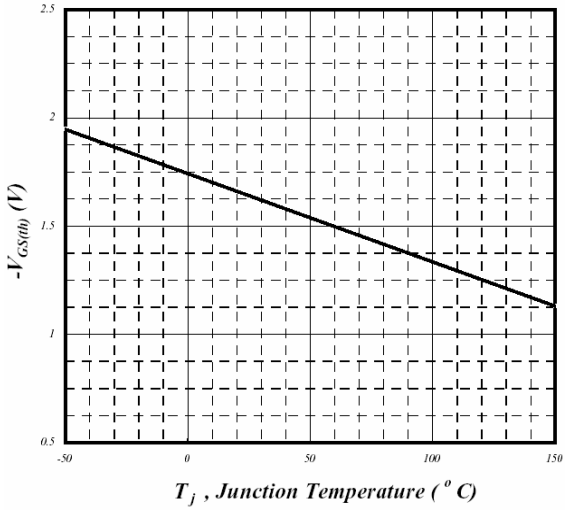

Fig 6. Gate Threshold Voltage v.s. Junction Temperature

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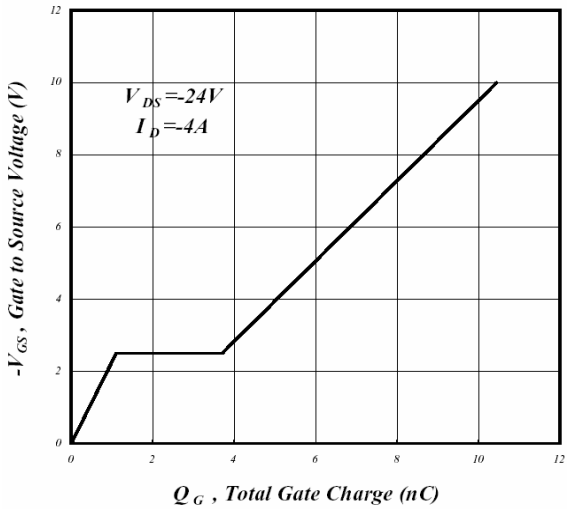

Fig 7. Gate Charge Characteristics

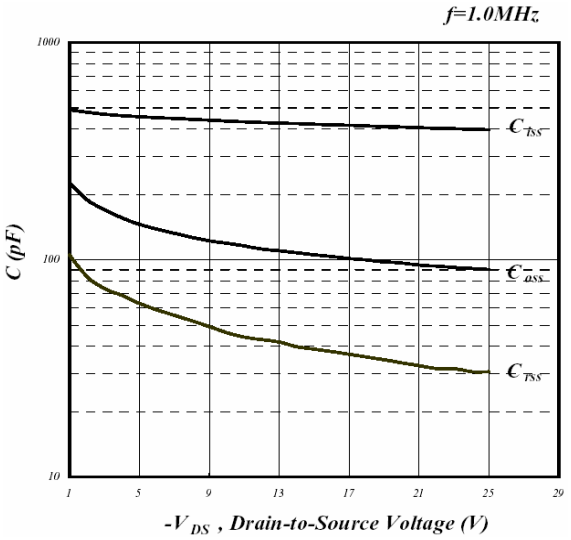

Fig 8. Typical Capacitance Characteristics

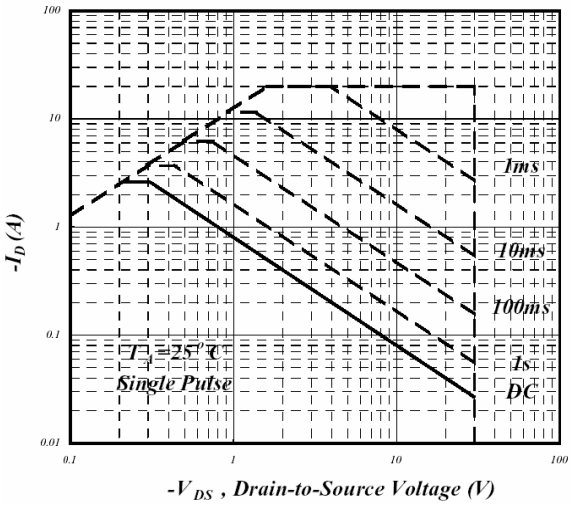

Fig 9. Maximum Safe Operating Area

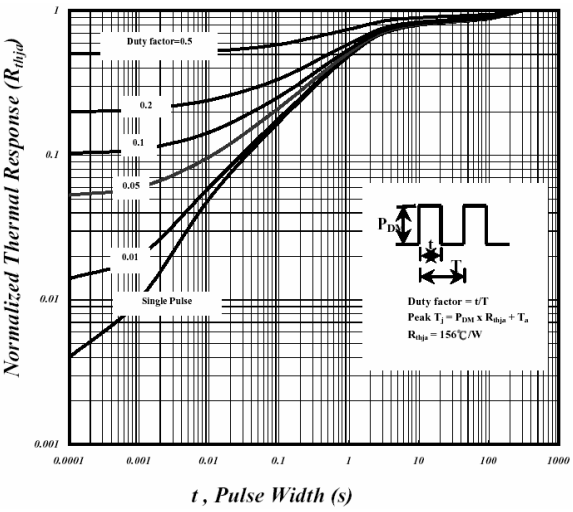

Fig 10. Effective Transient Thermal Impedance

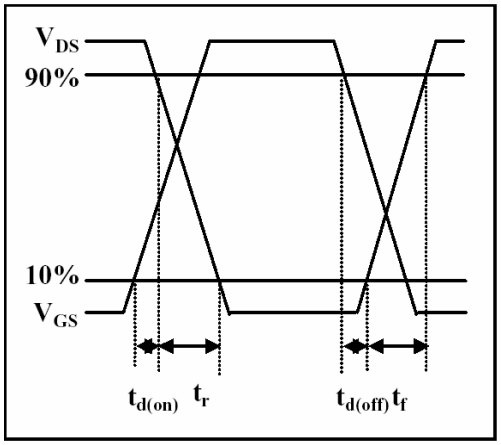

Fig 11. Switching Time Waveform

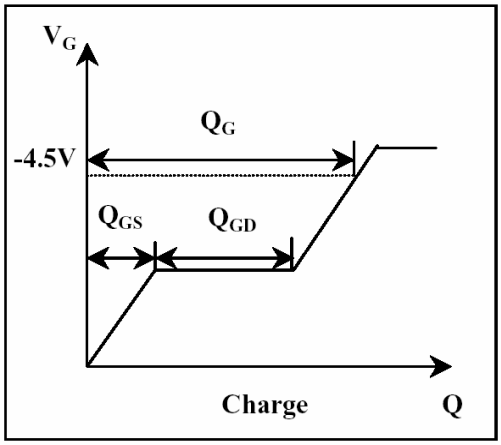

Fig 12. Gate Charge Waveform